



Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts,Customers Priority,Honest Operation,and Considerate Service",our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



## Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832

Email & Skype: info@chipsmall.com Web: www.chipsmall.com

Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China



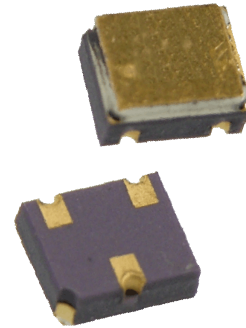
# Surface Mount PNP General Purpose Transistor

## 2N2907AUB (TX, TXV)



### Features:

- Ceramic 3 pin surface mount package (UBN)
- Miniature package to minimize circuit board area
- Hermetically sealed
- Footprint and pin-out matches SOT-23 package transistors
- Processed per MIL-PRF-19500/291



### Description:

The 2N2907AUB, 2N2907AUBTX and 2N2907AUBTXV are miniature, hermetically sealed, ceramic surface mount general purpose switching transistors. The miniature three pin ceramic package is ideal for upgrading commercial grade circuits to military reliability levels where plastic SOT-23 devices have been used. The "UB" suffix denotes the 3 terminal chip carrier package, type "B" per MIL-PRF-19500/291.

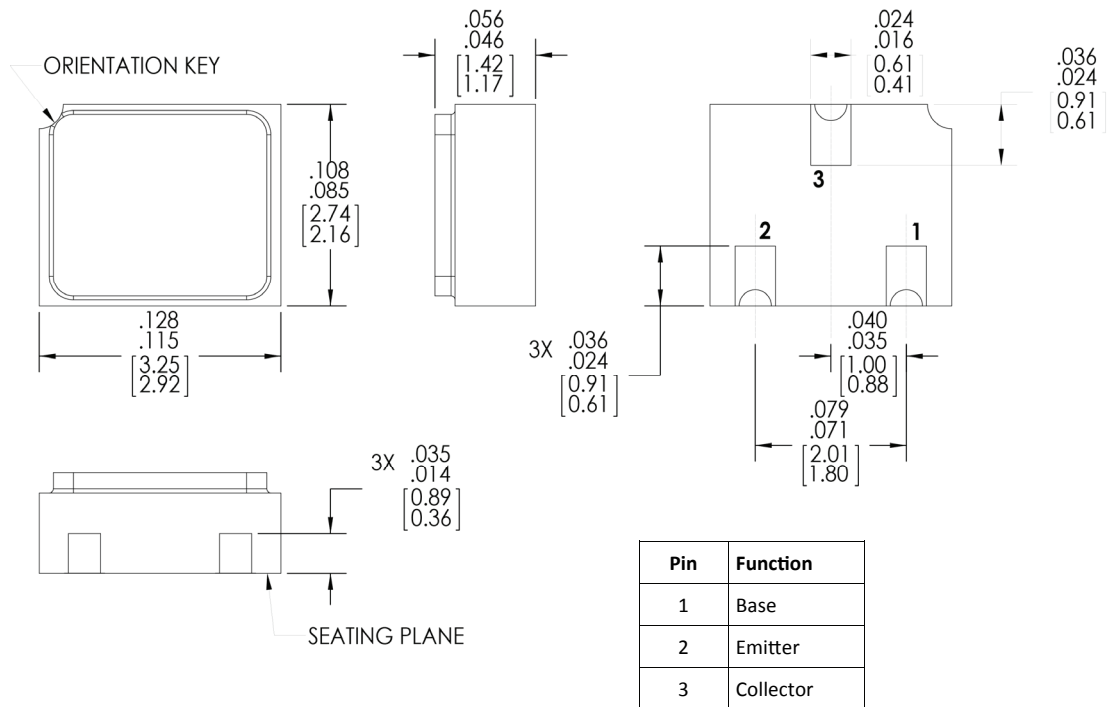
Typical screening and lot acceptance tests per MIL-PRF-19500/291.

The burn-in condition is  $V_{CB} = 30\text{ V}$ ,  $P_D = 200\text{ mW}$ ,  $T_A = 25^\circ\text{C}$ ,  $t = 80\text{ hrs}$ .

Refer to MIL-PRF-19500/291 for complete requirements. In addition, the TX and TXV versions receive 100% thermal response testing.

### Applications:

- General switching
- Amplification
- Signal processing
- Radio transmission
- Logic gates



General Note  
TT Electronics reserves the right to make changes in product specification without notice or liability. All information is subject to TT Electronics' own data and is considered accurate at time of going to print.

OPTEK Technology, Inc.  
1645 Wallace Drive, Carrollton, TX 75006 | Ph: +1 972 323 2200  
www.optekinc.com | www.ttelectronics.com

# Surface Mount PNP General Purpose Transistor

2N2907AUB (TX, TXV)



## Electrical Specifications

Absolute Maximum Ratings ( $T_A = 25^\circ\text{C}$ unless otherwise noted)	
Collector-Base Voltage	60V
Collector-Emitter Voltage	60V
Emitter-Base Voltage	5.0V
Collector Current-Continuous	600mA
Operating Junction Temperature ( $T_J$ )	-65° C to +200° C
Storage Junction Temperature ( $T_{stg}$ )	-65° C to +200° C
Power Dissipation @ $T_A = 25^\circ\text{C}$	0.5 W
Power Dissipation @ $T_c = 25^\circ\text{C}$	1.00 W <sup>(1)</sup>
Soldering Temperature (vapor phase reflow for 30 seconds)	215° C
Soldering Temperature (heated collet for 5 seconds)	260° C

Electrical Characteristics ( $T_A = 25^\circ\text{C}$ unless otherwise noted)						
SYMBOL	PARAMETER	MIN	MAX	UNITS	TEST CONDITIONS	
<b>OFF CHARACTERISTICS</b>						
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	60	-	V	$I_C = 10\ \mu\text{A}, I_E = 0$	
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	60	-	V	$I_C = 10\ \text{mA}, I_B = 0^{(2)}$	
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	5.0	-	V	$I_E = 10\ \mu\text{A}, I_C = 0$	
$I_{CBO}$	Collector-Base Cutoff Current		10	$\mu\text{A}$	$V_{CB} = 50\ \text{V}, I_E = 0$	
			10	$\mu\text{A}$	$V_{CB} = 50\ \text{V}, I_E = 0, T_A = 150^\circ\text{C}$	
$I_{EBO}$	Emitter-Base Cutoff Current		10	$\mu\text{A}$	$V_{CE} = 4.0\ \text{V}, I_C = 0$	
$I_{CES}$	Collector Emitter Cutoff Current		10	nA	$V_{EB} = 50\ \text{V}$	
<b>ON CHARACTERISTICS</b>						
$h_{FE}$	Forward-Current Transfer Ratio	75		-	$V_{CE} = 10\ \text{V}, I_C = 0.1\ \text{mA}$	
		100	450	-	$V_{CE} = 10\ \text{V}, I_C = 1.0\ \text{mA}$	
		100		-	$V_{CE} = 10\ \text{V}, I_C = 10\ \text{mA}$	
		100	300	-	$V_{CE} = 10\ \text{V}, I_C = 150\ \text{mA}^{(2)}$	
		50		-	$V_{CE} = 10\ \text{V}, I_C = 500\ \text{mA}^{(2)}$	
		50		-	$V_{CE} = 10\ \text{V}, I_C = 1.0\ \text{mA}, T_A = -55^\circ\text{C}$	

Note:

- Derate linearly 6.6 mW/°C above 25° C
- Pulse Width  $\leq 300\ \mu\text{s}$ , Duty Cycle  $\leq 2.0\%$

General Note  
TT Electronics reserves the right to make changes in product specification without notice or liability. All information is subject to TT Electronics' own data and is considered accurate at time of going to print.

OPTEK Technology, Inc.  
1645 Wallace Drive, Carrollton, TX 75006 | Ph: +1 972 323 2200  
www.optekinc.com | www.ttelectronics.com

# Surface Mount PNP General Purpose Transistor

2N2907AUB (TX, TXV)



Electrical Characteristics (T <sub>A</sub> = 25° C unless otherwise noted)					
SYMBOL	PARAMETER	MIN	MAX	UNITS	TEST CONDITIONS
<b>ON CHARACTERISTICS</b>					
V <sub>CE(SAT)</sub>	Collector-Emitter Saturation Voltage		0.40	V	I <sub>C</sub> = 150 mA, I <sub>B</sub> = 15 mA <sup>(2)</sup>
			1.60	V	I <sub>C</sub> = 500 mA, I <sub>B</sub> = 50 mA <sup>(2)</sup>
V <sub>BE(SAT)</sub>	Base-Emitter Saturation Voltage		1.30	V	I <sub>C</sub> = 150 mA, I <sub>B</sub> = 15 mA <sup>(2)</sup>
			2.60	V	I <sub>C</sub> = 500 mA, I <sub>B</sub> = 50 mA <sup>(2)</sup>
<b>SMALL-SIGNAL CHARACTERISTICS</b>					
h <sub>fe</sub>	Small Signal Forward Current Transfer Ratio	100		-	V <sub>CE</sub> = 10 V, I <sub>C</sub> = 1.0 mA, f = 1.0 kHz
h <sub>fe</sub>	Small Signal Forward Current Transfer Ratio	2.0		-	V <sub>CE</sub> = 20 V, I <sub>C</sub> = 20 mA, f = 100 MHz
C <sub>obo</sub>	Open Circuit Output Capacitance		8.0	pF	V <sub>CB</sub> = 10 V, 100 kHz ≤ f ≤ 1.0 MHz
C <sub>ibo</sub>	Input Capacitance (Output Open)		30	pF	V <sub>EB</sub> = 2.0 V, 100 kHz ≤ f ≤ 1.0 MHz
<b>SWITCHING CHARACTERISTICS</b>					
t <sub>on</sub>	Turn-On Time		45	ns	V <sub>CC</sub> = 30 V, I <sub>C</sub> = 150 mA, I <sub>B1</sub> = 15 mA
t <sub>off</sub>	Turn-Off Time		300	ns	V <sub>CC</sub> = 30 V, I <sub>C</sub> = 150 mA, I <sub>B1</sub> = I <sub>B2</sub> = 15 mA

**Note:**

1. Derate linearly 6.6 mW/°C above 25° C
2. Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%

General Note  
 TT Electronics reserves the right to make changes in product specification without notice or liability. All information is subject to TT Electronics' own data and is considered accurate at time of going to print.

OPTEK Technology, Inc.  
 1645 Wallace Drive, Carrollton, TX 75006 | Ph: +1 972 323 2200  
[www.optekinc.com](http://www.optekinc.com) | [www.ttelectronics.com](http://www.ttelectronics.com)

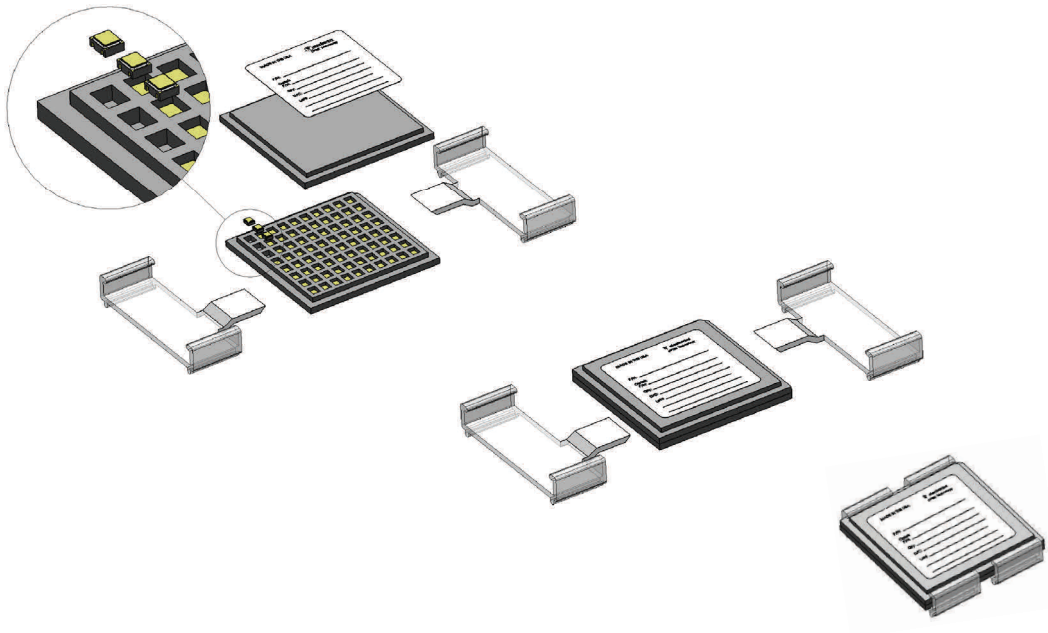
# Surface Mount PNP General Purpose Transistor

2N2907AUB (TX, TXV)



## Standard Packaging:

Waffle Pack



### Note:

1. Derate linearly 6.6 mW/°C above 25° C
2. Pulse Width  $\leq 300 \mu\text{s}$ , Duty Cycle  $\leq 2.0\%$

General Note  
TT Electronics reserves the right to make changes in product specification without notice or liability. All information is subject to TT Electronics' own data and is considered accurate at time of going to print.

OPTEK Technology, Inc.  
1645 Wallace Drive, Carrollton, TX 75006 | Ph: +1 972 323 2200  
[www.optekinc.com](http://www.optekinc.com) | [www.ttelectronics.com](http://www.ttelectronics.com)